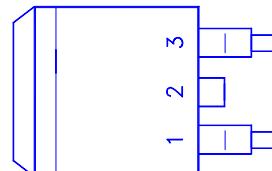
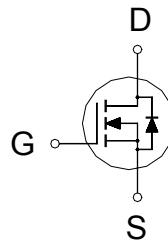


**NIKO-SEM**
**N-Channel Logic Level Enhancement  
Mode Field Effect Transistor**
**P3057LS**

TO-263

**PRODUCT SUMMARY**

$V_{(BR)DSS}$	$R_{DS(ON)}$	$I_D$
25	50mΩ	12A



1. GATE
2. DRAIN
3. SOURCE

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**ABSOLUTE MAXIMUM RATINGS ( $T_c = 25^\circ\text{C}$  Unless Otherwise Noted)**

PARAMETERS/TEST CONDITIONS	SYMBOL	LIMITS	UNITS
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	12	A
		8	
Pulsed Drain Current <sup>1</sup>	$I_{DM}$	45	
Avalanche Energy	$E_{AS}$	60	
Repetitive Avalanche Energy <sup>2</sup>	$E_{AR}$	3	mJ
Power Dissipation	$P_D$	48	W
		20	
Operating Junction & Storage Temperature Range	$T_j, T_{stg}$	-55 to 150	°C
Lead Temperature (1/16" from case for 10 sec.)	$T_L$	275	

**THERMAL RESISTANCE RATINGS**

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		3	
Junction-to-Ambient	$R_{\theta JA}$		75	°C / W
Case-to-Heatsink	$R_{\theta CS}$	1		

<sup>1</sup>Pulse width limited by maximum junction temperature.<sup>2</sup>Duty cycle ≤ 1%**ELECTRICAL CHARACTERISTICS ( $T_c = 25^\circ\text{C}$ , Unless Otherwise Noted)**

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
<b>STATIC</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu\text{A}$	25			V
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	0.8	1.2	2.5	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 20V$			$\pm 250$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 20V, V_{GS} = 0V$			25	$\mu\text{A}$
		$V_{DS} = 20V, V_{GS} = 0V, T_J = 125^\circ\text{C}$			250	

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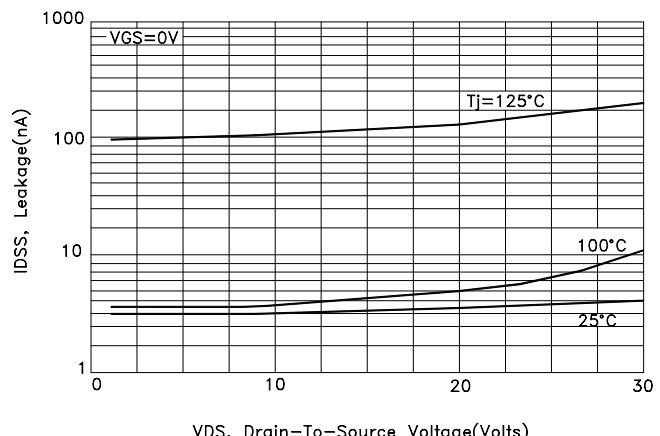
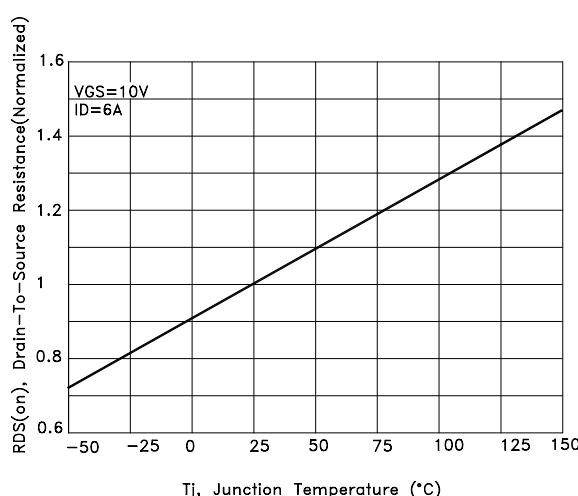
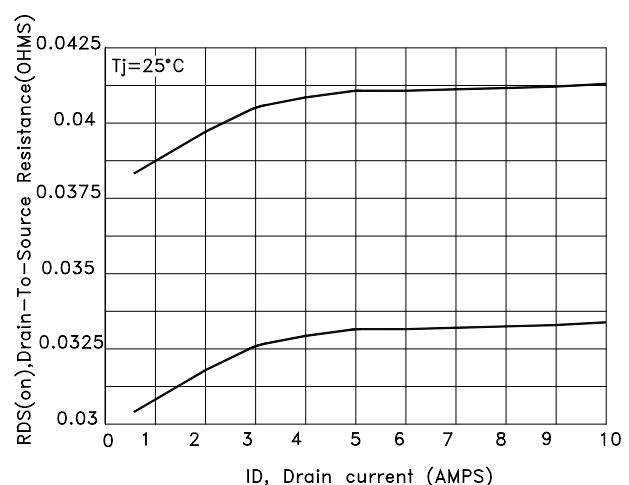
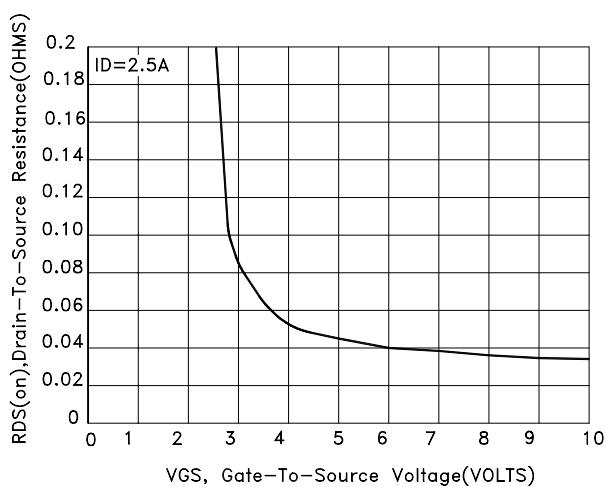
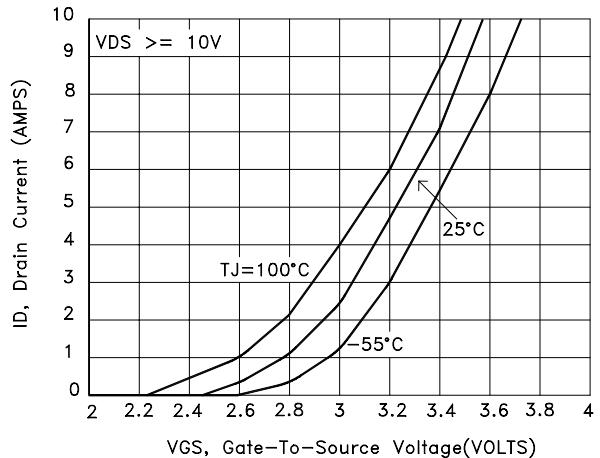
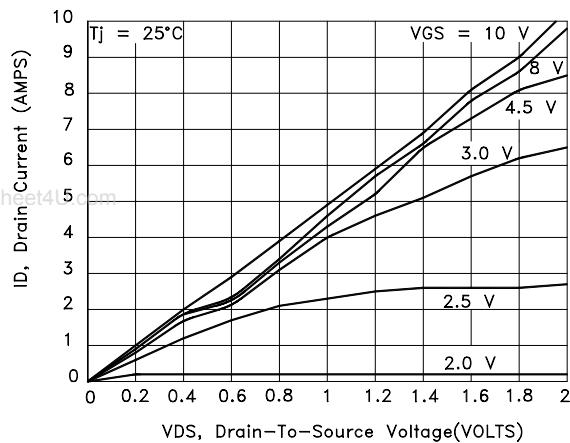
On-State Drain Current <sup>1</sup>	$I_{D(ON)}$	$V_{DS} = 10V, V_{GS} = 10V$	12			A
Drain-Source On-State Resistance <sup>1</sup>	$R_{DS(ON)}$	$V_{GS} = 5V, I_D = 12A$	70	115		$m\Omega$
		$V_{GS} = 10V, I_D = 12A$	48	85		
Forward Transconductance <sup>1</sup>	$g_{fs}$	$V_{DS} = 15V, I_D = 12A$	16			S
<b>DYNAMIC</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$	450			$pF$
Output Capacitance	$C_{oss}$		200			
Reverse Transfer Capacitance	$C_{rss}$		60			
Total Gate Charge <sup>2</sup>	$Q_g$	$V_{DS} = 0.5V_{(BR)DSS}, V_{GS} = 10V, I_D = 6A$	15			$nC$
Gate-Source Charge <sup>2</sup>	$Q_{gs}$		2.0			
Gate-Drain Charge <sup>2</sup>	$Q_{gd}$		7.0			
Turn-On Delay Time <sup>2</sup>	$t_{d(on)}$	$V_{DS} = 15V, R_L = 1\Omega$ $I_D \cong 12A, V_{GS} = 10V, R_{GS} = 2.5\Omega$	6.0			$nS$
Rise Time <sup>2</sup>	$t_r$		6.0			
Turn-Off Delay Time <sup>2</sup>	$t_{d(off)}$		20			
Fall Time <sup>2</sup>	$t_f$		5.0			
<b>SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (<math>T_C = 25^\circ C</math>)</b>						
Continuous Current	$I_S$			12		A
Pulsed Current <sup>3</sup>	$I_{SM}$			20		
Forward Voltage <sup>1</sup>	$V_{SD}$	$I_F = I_S, V_{GS} = 0V$		1.5	V	
Reverse Recovery Time	$t_{rr}$	$I_F = I_S, dI_F/dt = 100A / \mu s$	30		$nS$	
Peak Reverse Recovery Current	$I_{RM(REC)}$		15		A	
Reverse Recovery Charge	$Q_{rr}$		0.043		$\mu C$	

<sup>1</sup>Pulse test : Pulse Width  $\leq 300 \mu sec$ , Duty Cycle  $\leq 2\%$ .<sup>2</sup>Independent of operating temperature.<sup>3</sup>Pulse width limited by maximum junction temperature.**REMARK: THE PRODUCT MARKED WITH "P3057LS", DATE CODE or LOT #**

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**TO-263**



TO-263 (D<sup>2</sup>PAK) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	14.5	15	15.8	H	1.0	1.5	1.8
B	4.2		4.7	I	9.8		10.3
C	1.20		1.35	J		6.5	
D		2.8		K		1.5	
E	0.3	0.4	0.5	L	0.7		1.4
F	-0.102		0.203	M	4.83	5.08	5.33
G	8.5	9	9.5	N			

